IN THE CLAIMS

1 (Previously Presented). A method comprising:

developing a patterned photoresist;

lowering the glass transition temperature of the photoresist using supercritical carbon dioxide fluid; and

reflowing the photoresist after lowering the glass transition temperature.

Claims 2-6 (Canceled).

7 (Original). The method of claim 1 including applying a plasticizer that improves the etch resistance of the photoresist.

8 (Original). The method of claim 1 wherein applying a plasticizer includes diffusing a plasticizer into the photoresist.

9 (Original). The method of claim 8 including diffusing a plasticizer in a vapor phase into the photoresist.

10 (Original). The method of claim 1 including controlling the amount of reflow by volatilizing the plasticizer during reflow.

11 (Original). The method of claim 1 including applying the plasticizer in liquid carbon dioxide.

12 (Original). The method of claim 1 including controlling the amount of reflow by cooling the photoresist.

Claims 13-27 (Canceled).

28 (Previously Presented). A method comprising:

developing a patterned photoresist;

lowering the glass transition temperature of the photoresist during the develop rinse; and

reflowing the photoresist after lowering the glass transition temperature.

29 (Previously Presented). The method of claim 28 including applying a plasticizer that improves the etch resistance of the photoresist.

30 (Previously Presented). The method of claim 28 wherein applying a plasticizer includes diffusing a plasticizer into the photoresist.

31 (Previously Presented). The method of claim 30 including diffusing a plasticizer in a vapor phase into the photoresist.

32 (Previously Presented). The method of claim 28 including controlling the amount of reflow by volatilizing the plasticizer during reflow.

33 (Previously Presented). The method of claim 28 including applying the plasticizer in liquid carbon dioxide.

34 (Previously Presented). The method of claim 28 including controlling the amount of reflow by cooling the photoresist.